

# 3rd Intensive Discussion on Growth of Nitride Semiconductors

January 16 - 18, 2017  
Auditorium, Bldg. 2, Institute for Materials Research,  
Tohoku University, Sendai, Japan

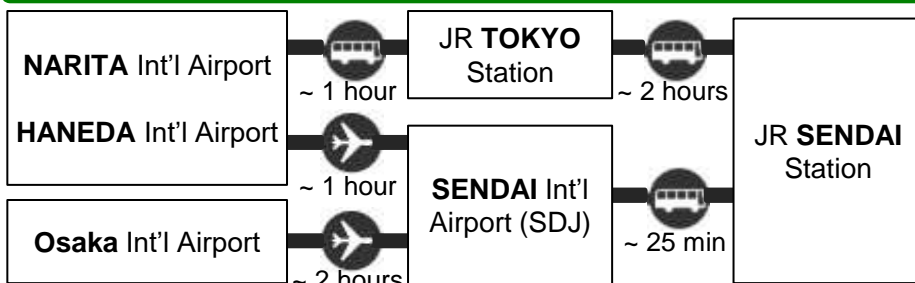
## Prospectus of the workshop

The purpose of the workshop is to analyze the status quo, find the direction to take in the future and the problems that need to be solved in the field of crystal growth of nitride semiconductors. To achieve this, the number of participants is limited to 50 persons including researchers from abroad, and the straightforward discussions are greatly encouraged among the selected professionals. Participants are expected to have common understandings in the current technologies and to find out the way to solve problems in the crystal growth. In the workshop, some selected topics will be presented at the beginning of each session, and the participants voluntarily present their data, which is followed by deep-and-intensive discussion. This style is not common but will bring us significant outcome. We are looking forward to seeing you all here in Heart of Northeast area of Japan, City of Sendai.

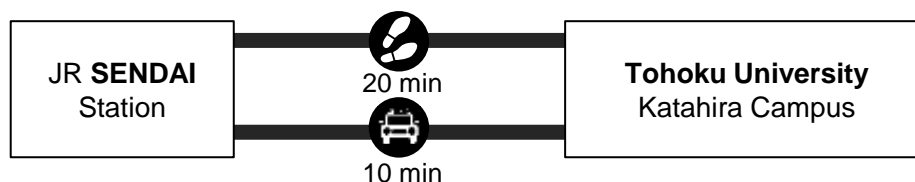
## Access to Tohoku Univ.



## Tokyo or Osaka to SENDAI



## SENDAI station to Tohoku University



## Registration

**Registration Fee: 20,000 JPY**

**Registration Deadline: January 13th, 2017**

- All the participants are required to contact the agency below.

### Contact:

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## Committee Members

### Chairs:

Takashi Matsuoka IMR, Tohoku Univ.  
Hiroyuki Fukuyama IMRAM, Tohoku Univ.

### Members:

Makoto Ohtsuka IMRAM, Tohoku Univ.  
Kazunobu Kojima IMRAM, Tohoku Univ.  
Masayoshi Adachi IMRAM, Tohoku Univ.  
Shigeyuki Kuboya IMR, Tohoku Univ.  
Momoko Deura IMR, Tohoku Univ.  
Tomoyuki Tanikawa IMR, Tohoku Univ.  
Miho Matsuura IMR, Tohoku Univ.

# Technical Program

Time	Topics	Speakers
<b>16 (Mon)</b>		
18:00 – 19:00	Welcome Reception	
<b>17 (Tue)</b>		
8:30 – 9:00	Registration	
9:00 – 9:10	Opening	
9:10 – 11:30	<b>Electronic Devices I</b>	<b>M. Kuzuhara (Fukui University, Japan)</b>
		<b>T. Suemitsu (Tohoku University, Japan)</b>
		<b>J. Kuzmik (Slovak Academy of Sciences, Slovakia)</b>
		<b>K. Prasertsuk (Tohoku University, Japan)</b>
11:30 – 13:00	Lunch	
13:00 – 14:10	<b>Crystal Growth I</b>	<b>Y. Otoki (SCIOCS, Japan)</b>
		<b>M. Iwinska (UNIPRESS, Poland)</b>
14:10 – 14:25	Break	
14:25 – 16:10	<b>Crystal Growth II</b>	<b>M. Adachi (Tohoku University, Japan)</b>
		<b>M. Balaji (University of Madras, India)</b>
		<b>V. Sabarinathan (Manonmaniam Sundaranar Univ. India)</b>
16:10 – 16:25	Break	
16:25 – 18:10	<b>Characterization for Devices</b>	<b>O. Ueda (Kanazawa Institute of Technology, Japan)</b>
		<b>A. Sakai (Osaka University, Japan)</b>
		<b>Y. Ishitani (Chiba University, Japan)</b>
19:00 –	Banquet	at The Westin Sendai
<b>18 (Wed)</b>		
8:30 – 9:00	Registration	
9:00 – 9:10	Information	
9:10 – 11:30	<b>Electronic Devices II</b>	<b>T. Kimoto (Kyoto University, Japan)</b>
		<b>T. Hashizume (Hokkaido University, Japan)</b>
		<b>S. Takashima (Fuji Electric Co., Ltd., Japan)</b>
		<b>T. Kachi (Nagoya University, Japan)</b>
11:30 –	Closing	